

N-channel 600 V, 0.280 Ω typ., 11 A MDmesh™ DM2 with fast diode Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - preliminary data

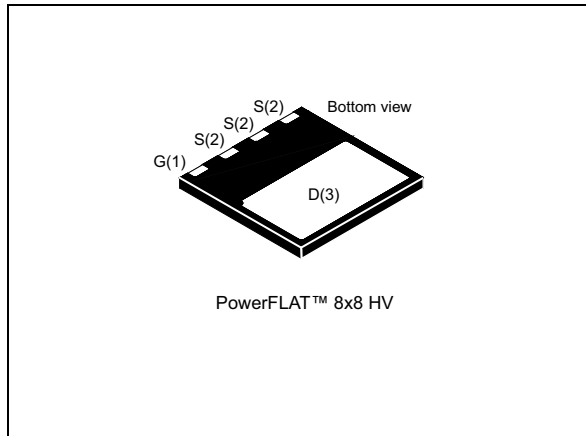
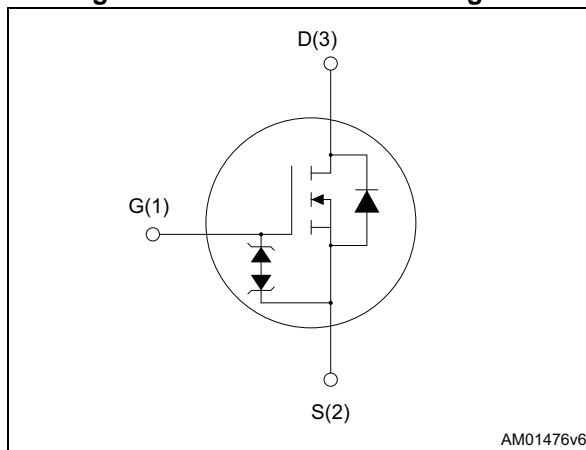


Figure 1. Internal schematic diagram



Features

Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on)max}$	I_D
STL19N60DM2	650 V	0.320 Ω	11 A

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance $R_{DS(on)}$
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high voltage N-channel Power MOSFET is part of the MDmesh DM2 fast recovery diode series. It offers very low recovery charge and time (Q_{rr} , t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL19N60DM2	19N60DM2	PowerFLAT™ 8x8 HV	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	11	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6.8	A
$I_{DM}^{(1),(2)}$	Drain current (pulsed)	44	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	TBD	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	TBD	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	40	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 11\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
4. $V_{DS} \leq 480\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.39	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-ambient max	45	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of inch^2 , 2oz Cu.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 600\text{V}$			1	μA
		$V_{GS} = 0, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$		0.280	0.320	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	TBD	-	pF
C_{oss}	Output capacitance		-	TBD	-	pF
C_{rss}	Reverse transfer capacitance		-	TBD	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}, V_{GS} = 0$	-	TBD	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$		5.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 11\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 3)	-	21	-	nC
Q_{gs}	Gate-source charge		-	TBD	-	nC
Q_{gd}	Gate-drain charge		-	TBD	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 5.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 2 and 7)	-	TBD	-	ns
t_r	Voltage rise time		-	TBD	-	ns
$t_{d(off)}$	Turn-off delay time		-	TBD	-	ns
t_f	Current fall time		-	TBD	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		11	A
$I_{SDM}^{(1),(2)}$	Source-drain current (pulsed)		-		44	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD} = 11\text{ A}$, $V_{GS} = 0$	-		1.5	V
$t_{rr}^{(4)}$	Reverse recovery time	$I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 4)	-	120		ns
$Q_{rr}^{(4)}$	Reverse recovery charge		-	TBD		μC
$I_{RRM}^{(4)}$	Reverse recovery current		-	TBD		A
$t_{rr}^{(4)}$	Reverse recovery time	$I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 4)	-	TBD		ns
$Q_{rr}^{(4)}$	Reverse recovery charge		-	TBD		μC
$I_{RRM}^{(4)}$	Reverse recovery current		-	TBD		A

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area
3. Pulsed: pulse duration = 300 μs , duty cycle 1.5%
4. Typical values are referring to the test conditions of the same die housed in through hole package.

The built-in back-to-back Zener diodes have been specifically designed to enhance the ESD capability of the device. The Zener voltage is appropriate for efficient and cost-effective intervention to protect the device integrity. These integrated Zener diodes thus eliminate the need for external components.

3 Test circuits

Figure 2. Switching times test circuit for resistive load

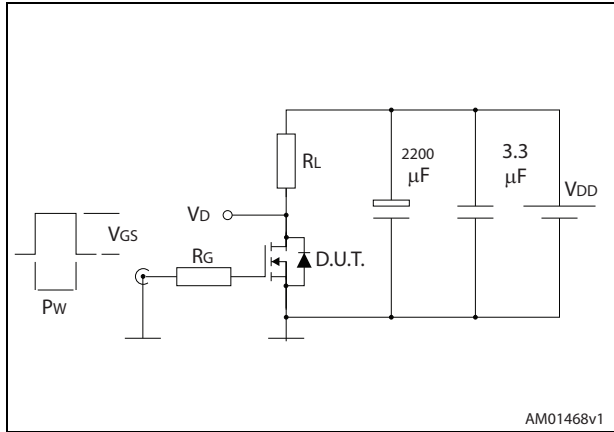


Figure 3. Gate charge test circuit

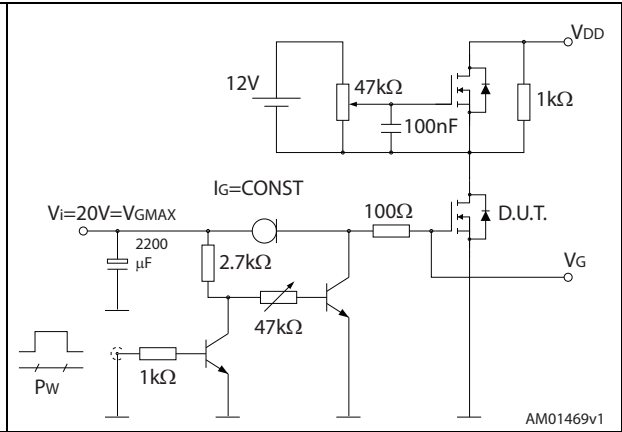


Figure 4. Test circuit for inductive load switching and diode recovery times

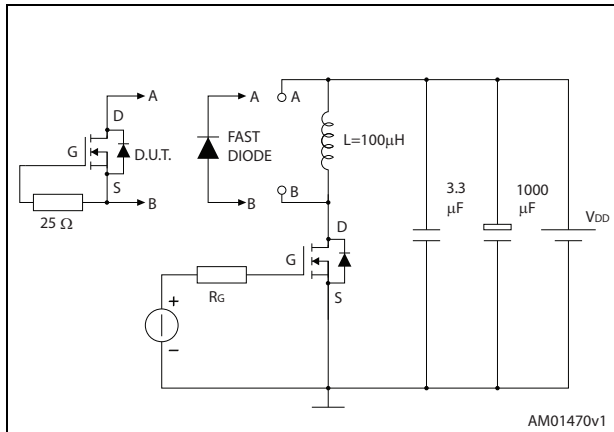


Figure 5. Unclamped inductive load test circuit

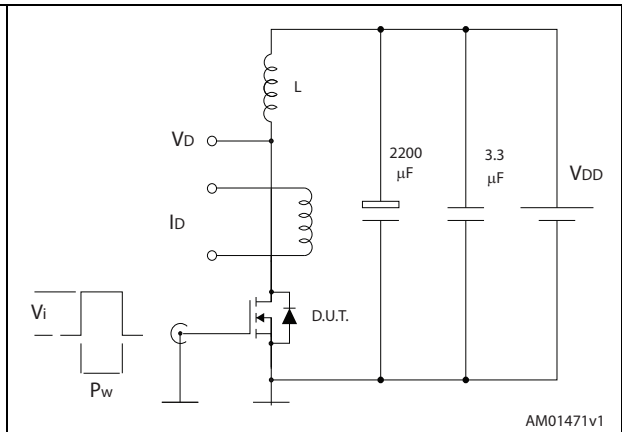


Figure 6. Unclamped inductive waveform

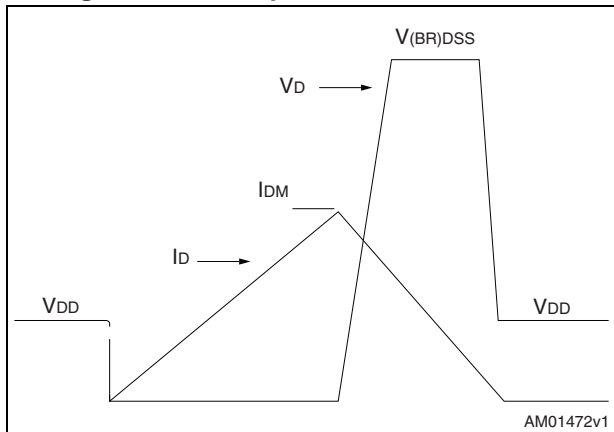
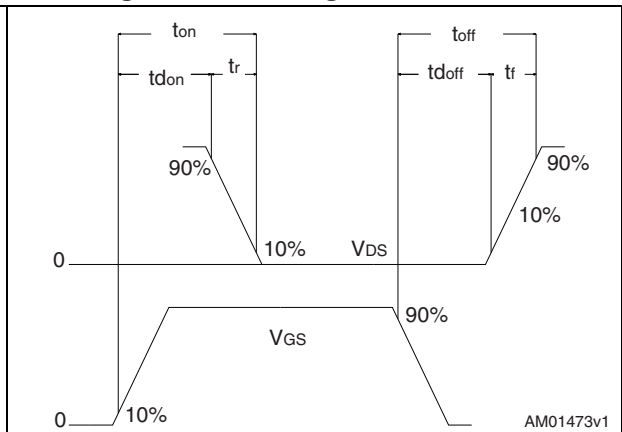


Figure 7. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 8. PowerFLAT™ 8x8 HV drawing mechanical data

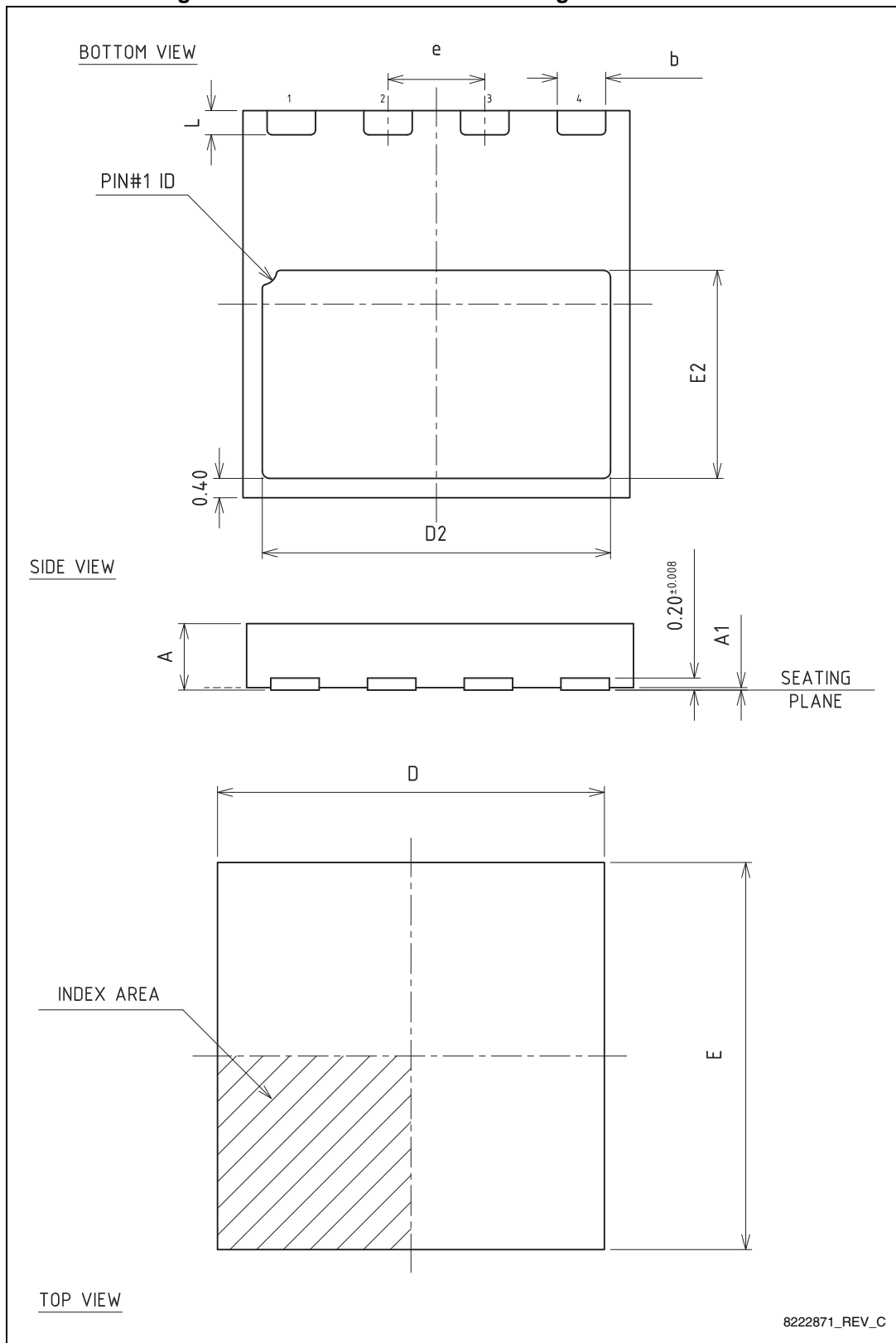
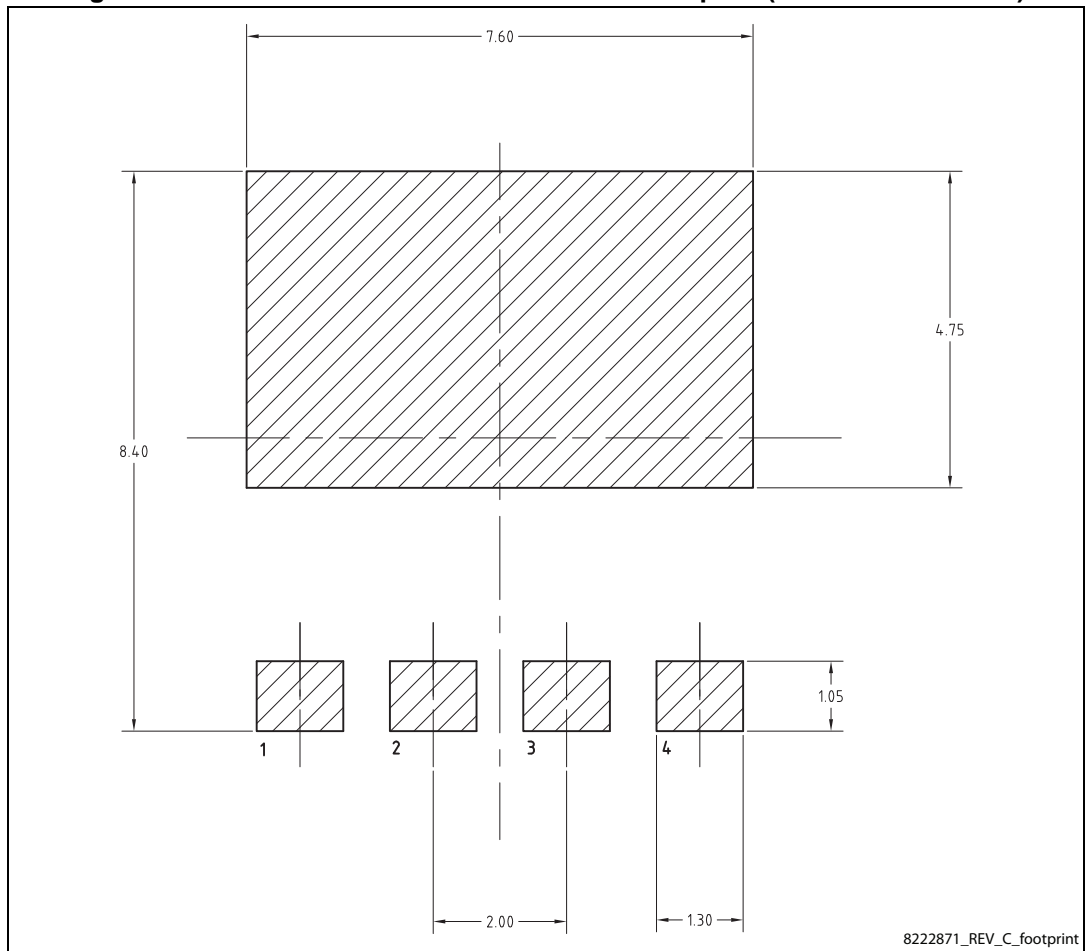


Table 8. PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60

Figure 9. PowerFLAT™ 8x8 HV recommended footprint (dimensions in mm.)



5 Packaging mechanical data

Figure 10. PowerFLAT™ 8x8 HV tape

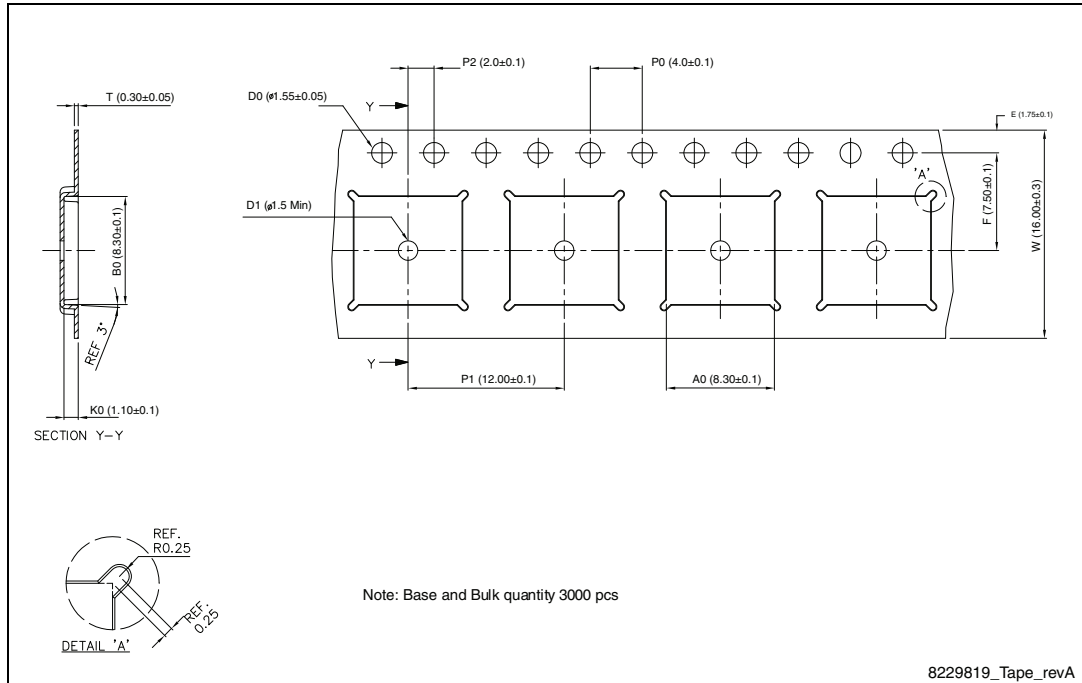


Figure 11. PowerFLAT™ 8x8 HV package orientation in carrier tape

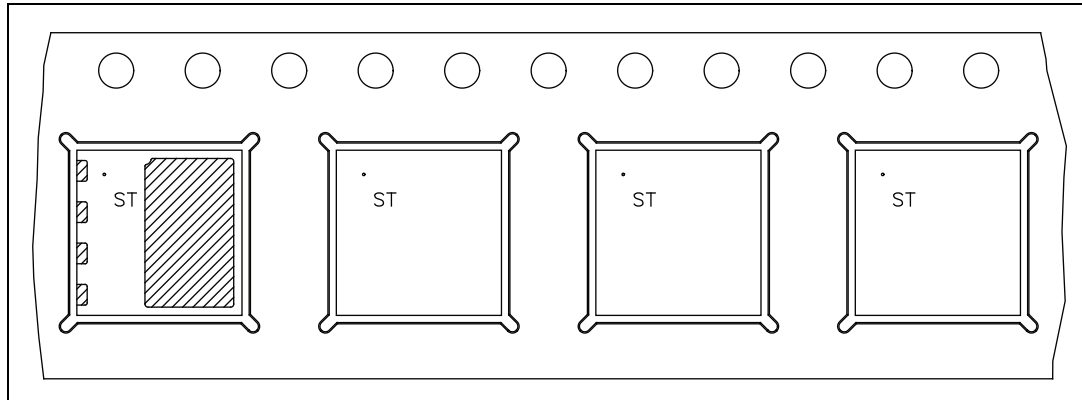
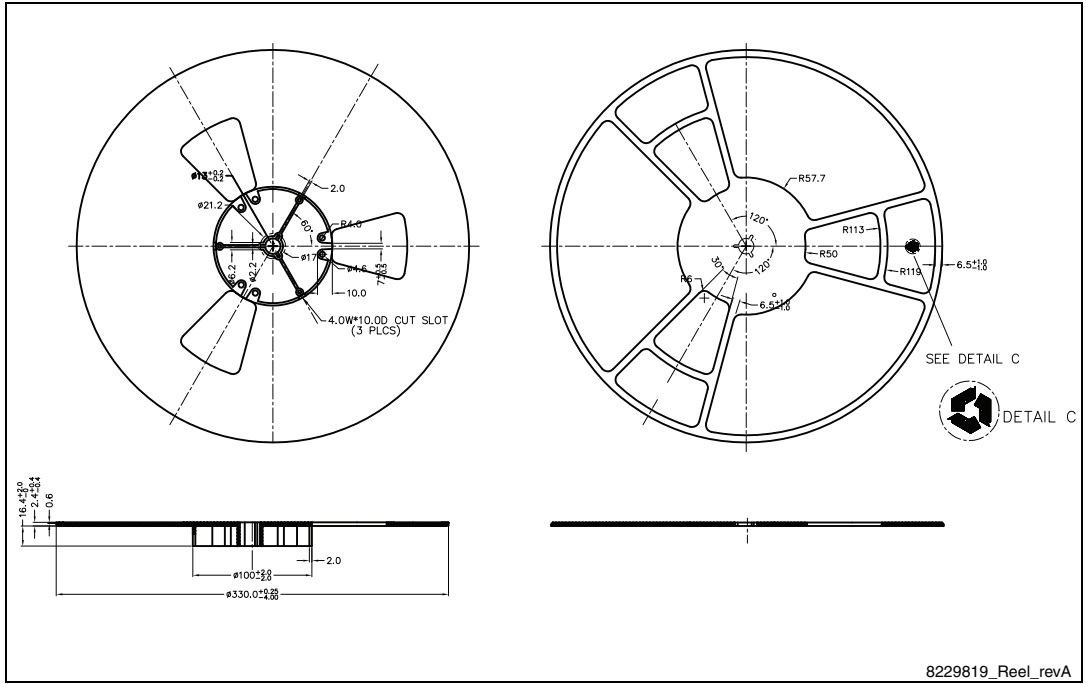


Figure 12. PowerFLAT™ 8x8 HV reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
08-Aug-2014	1	First release.

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